

IN THE CLAIMS:

The status of each claim that has been introduced in the above-referenced application is identified in the ensuing listing of the claims. This listing of the claims replaces all previously submitted claims listings.

1. (Currently amended) A semiconductor device, comprising:
a semiconductor substrate including an active surface;
at least one conductive line disposed upon ~~said~~the active surface, ~~said~~the at least one conductive line being flanked by sidewall spacers;
an undoped silicon dioxide cap disposed over and in contact with ~~said~~the at least one conductive line;
a passivation layer over ~~said~~the undoped silicon dioxide cap; and
at least one contact aperture defined through ~~said~~the passivation layer and including at least one sidewall extending substantially perpendicularly relative to ~~said~~the semiconductor substrate, at least a portion of ~~said~~the at least one sidewall terminating at ~~said~~an interface between the passivation layer and the undoped silicon dioxide cap.
2. (Currently amended) The semiconductor device of claim 1, wherein ~~said~~the at least one conductive line comprises a word line.
3. (Currently amended) The semiconductor device of claim 1, wherein ~~said~~the passivation layer comprises doped silicon dioxide.
4. (Currently amended) The semiconductor device of claim 1, wherein ~~said~~the passivation layer comprises borophosphosilicate glass, phosphosilicate glass, or borosilicate glass.

5. (Currently amended) The semiconductor device of claim 1, wherein ~~said~~the undoped silicon dioxide cap is at least partially exposed through ~~said~~the at least one contact aperture.

6. (Currently amended) A semiconductor device, comprising:
a semiconductor substrate;
at least one undoped silicon oxide structure; and
at least one doped silicon oxide structure over ~~said~~the at least one undoped silicon oxide structure
and having at least one sidewall substantially perpendicular to a plane of ~~said~~the
semiconductor substrate, at least a portion of ~~said~~the at least one sidewall terminating at
~~said~~ an interface between the at least one doped silicon dioxide structure and the at least
one undoped silicon oxide structure.

7. (Currently amended) The semiconductor device of claim 6, wherein ~~said~~the at least one sidewall comprises a sidewall of an aperture.

8. (Currently amended) The semiconductor device of claim 6, wherein ~~said~~the at least one sidewall at least partially defines an aperture through ~~said~~the at least one doped silicon oxide structure.

9. (Currently amended) The semiconductor device of claim 6, wherein ~~said~~the at least one doped silicon oxide structure comprises borophosphosilicate glass, phosphosilicate glass, or borosilicate glass.

10. (Currently amended) The semiconductor device of claim 6, wherein ~~said~~the at least one undoped silicon oxide structure is at least partially located over a conductive structure.

11. (Currently amended) The semiconductor device of claim 10, wherein ~~said~~the at least one undoped silicon oxide structure comprises an insulative cap over a conductive line.

12. (Currently amended) The semiconductor device of claim 11, wherein ~~said~~the insulative cap is partially exposed through an aperture of ~~said~~the at least one doped silicon oxide structure defined by ~~said~~the at least one sidewall.

13. (Currently amended) The semiconductor device of claim 6, wherein ~~said~~the at least one undoped silicon oxide structure is at least partially exposed adjacent ~~said~~the at least one sidewall.